

DISPLAY DEVICE

Patent Number: JP10274785
Publication date: 1998-10-13
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Requested Patent: JP10274785
Application Number: JP19970081139 19970331
Priority Number(s):
IPC Classification: G02F1/136
EC Classification:
Equivalents:

Abstract

PROBLEM TO BE SOLVED: To hold the area that the source wire of a pixel area occupies as minimum as possible and to obtain a high aperture rate by arranging and wiring thin film transistors in more than one layer.

SOLUTION: On the entire top surface of a glass substrate 1, an insulating protection film 2 is formed of, for example, silicon dioxide. On its top surface, a semiconductor film 3 is formed and then patterned to form an active layer. Then a gate insulating film 4 and a gate wire 5 are formed on the top surface of the glass substrate 1 including this active layer. A source area 6 and a drain area 7 is developed in the active layer by a method such as ion doping from above it. Silicon dioxide is filmed as an inter-layer insulating film 8 on the top surface and a contact hole is bored in the inter-layer insulating film 8 and the source area of the gate insulating film 4 by using photolithography and etching technology. Then a conductive metal material is filmed as a source wire material to fill the contact hole.

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